FWE08N130RH

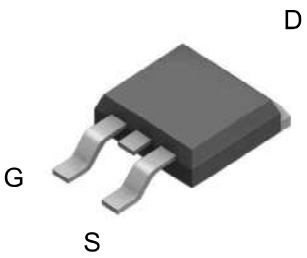
Single N-channel Trench MOSFET 80V

General Description

The FWE08N130RH uses advanced Fullwin's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality These devices can also be utilized in industrial applications such as Low Power Drives of E-bike (E-Vehicles), DC/DC converter, and general purpose applications.

Features

- V_{DS} = 80V
- I_D = 120 A @V_{GS} = 10V
- $R_{DS(ON)}$ < 5.0 mΩ @V_{GS} = 10V
- 175 °C operating temperature
- 100% UIL Tested
- 100% Rg Tested
- 100% △V_{DS} Tested



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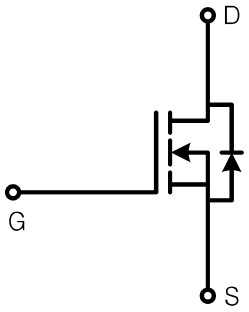

Absolute Maximum Ratings (T_J = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (1)	T_C=25°C (Silicon Limited)	I_D	132	A
	T_C=25°C (Package Limited)		120	
	T_C=100°C (Silicon Limited)		93	
	T_A=25°C		14.9	
Pulsed Drain Current (2)		I_{DM}	480	
Power Dissipation	T_C=25°C	P_D	188	W
	T_C=100°C		94	
	T_A=25°C		2.4	
Single Pulse Avalanche Energy (3)		E_{AS}	200	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~175	°C

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient (1)	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.8	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
FWE08N130RH	-55~175°C	TO-263	Reel	Halogen Free

Electrical Characteristics (T_J =25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	80	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.4		3.8	
Drain Cut-Off Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V	-	-	1.0	uA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 50A		4.0	5.0	mΩ
Forward Transconductance	g_{fs}	V_{DS} = 10V, I_D = 50A	-	81	-	S
Dynamic Characteristics						
Total Gate Charge	$Q_{g(10V)}$	V_{DD} = 40V, I_D = 50A, V_{GS} = 10V	-	61	-	nC
Gate-Source Charge	Q_{gs}		-	18	-	
Gate-Drain Charge	Q_{gd}		-	15	-	
Input Capacitance	C_{iss}	V_{DS} = 40V, V_{GS} = 0V, f = 1.0MHz	-	4150	-	pF
Reverse Transfer Capacitance	C_{rss}		-	40	-	
Output Capacitance	C_{oss}		-	970	-	
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 10V, V_{DD} = 40V, I_D = 50A, R_G =3Ω,	-	24	-	ns
Rise Time	t_r		-	13	-	
Turn-Off Delay Time	$t_{d(off)}$		-	43	-	
Fall Time	t_f		-	14	-	
Gate Resistance	R_g	f=1.0 MHz	-	2.5	-	Ω
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	I_S = 50A, V_{GS} = 0V	-	0.9	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 50A, dI/dt = 100A/μs	-	86	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	270	-	nC

Note : 1. Surface mounted FR-4 board by JEDEC (jesd51-7)
2. Pulse width limited by T_{jmax}
3. E_{AS} is tested at starting Tj = 25℃, L = 1.0mH, I_{AS} = 20 A, V_{DD} = 50V, V_{GS} = 10V

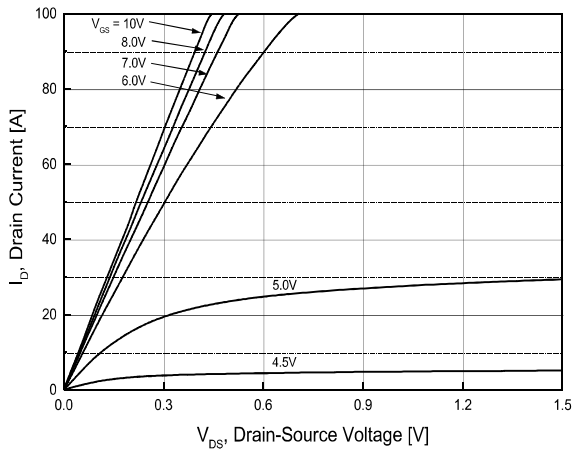

Fig.1 On-Region Characteristics

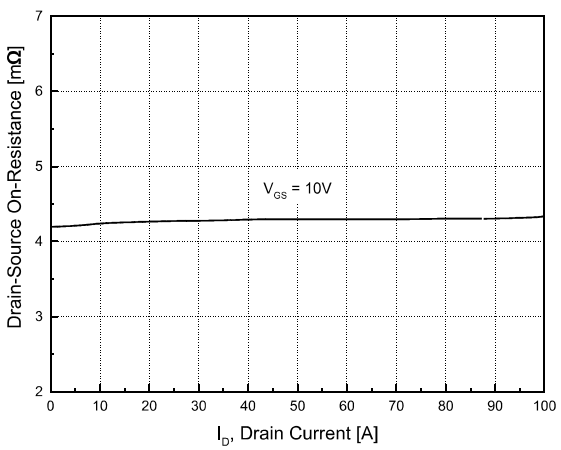

Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

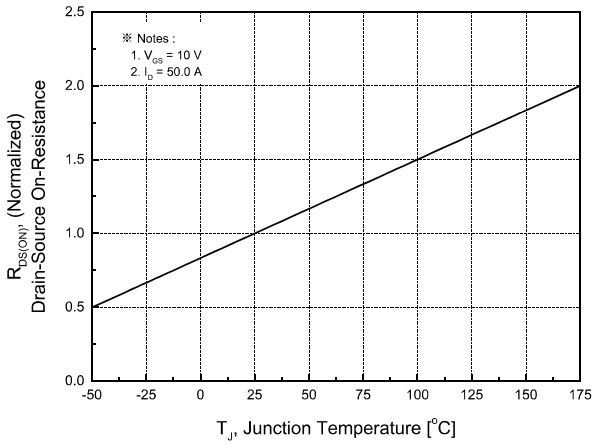

Fig.3 On-Resistance Variation with Temperature

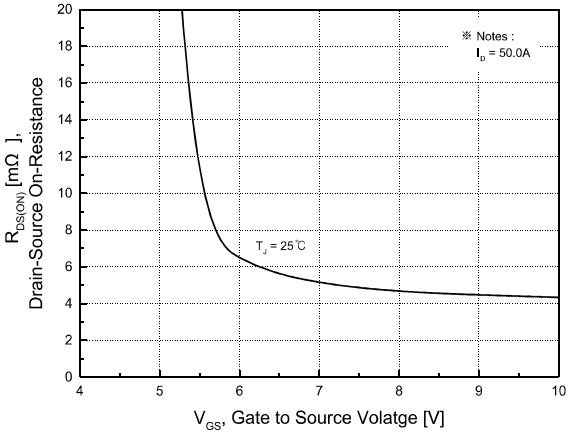

Fig.4 On-Resistance Variation with Gate to Source Voltage

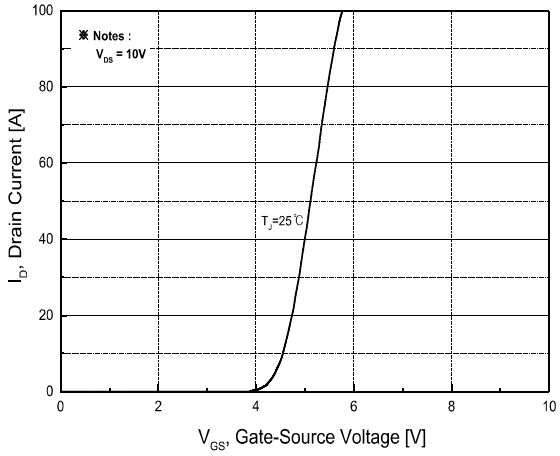

Fig.5 Transfer Characteristics

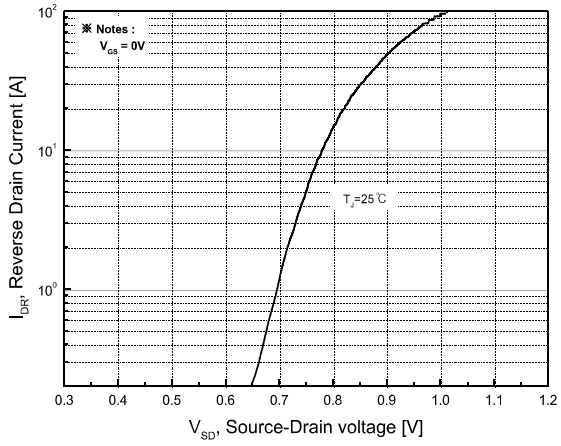

Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

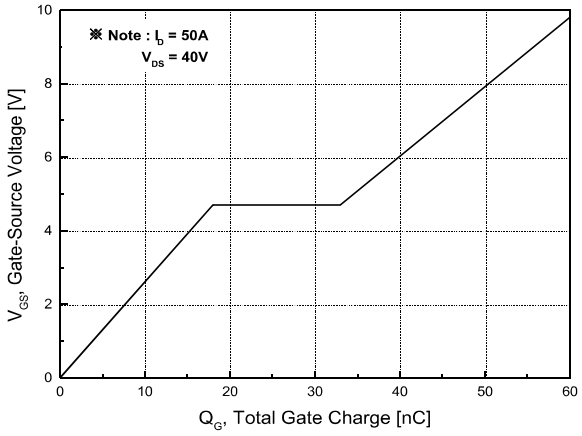

Fig.7 Gate Charge Characteristics

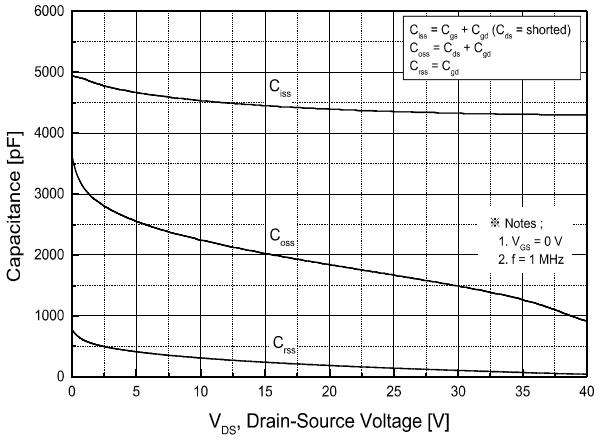

Fig.8 Capacitance Characteristics

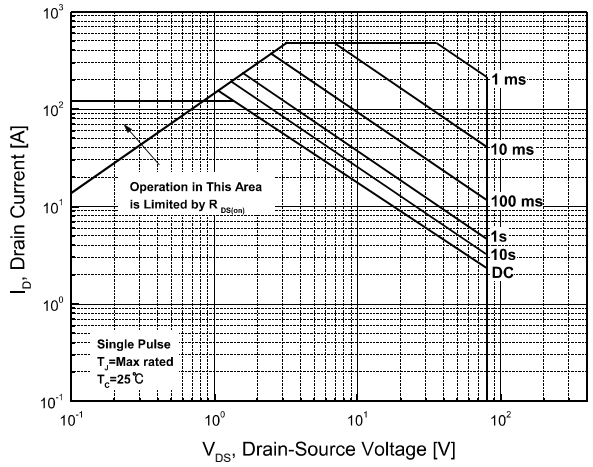

Fig.9 Maximum Safe Operating Area

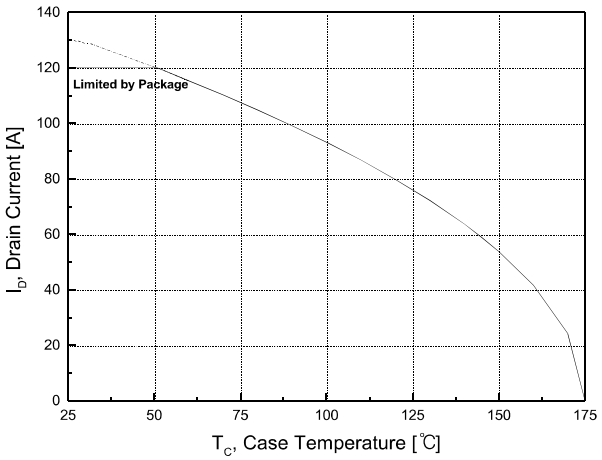

Fig.10 Maximum Drain Current vs. Case Temperature

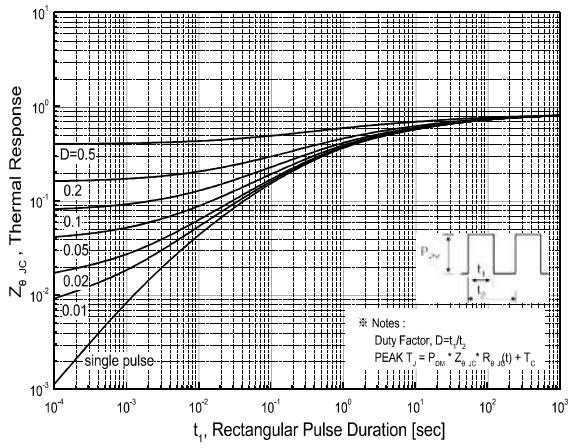

Fig.11 Transient Thermal Response Curve

Package Dimension

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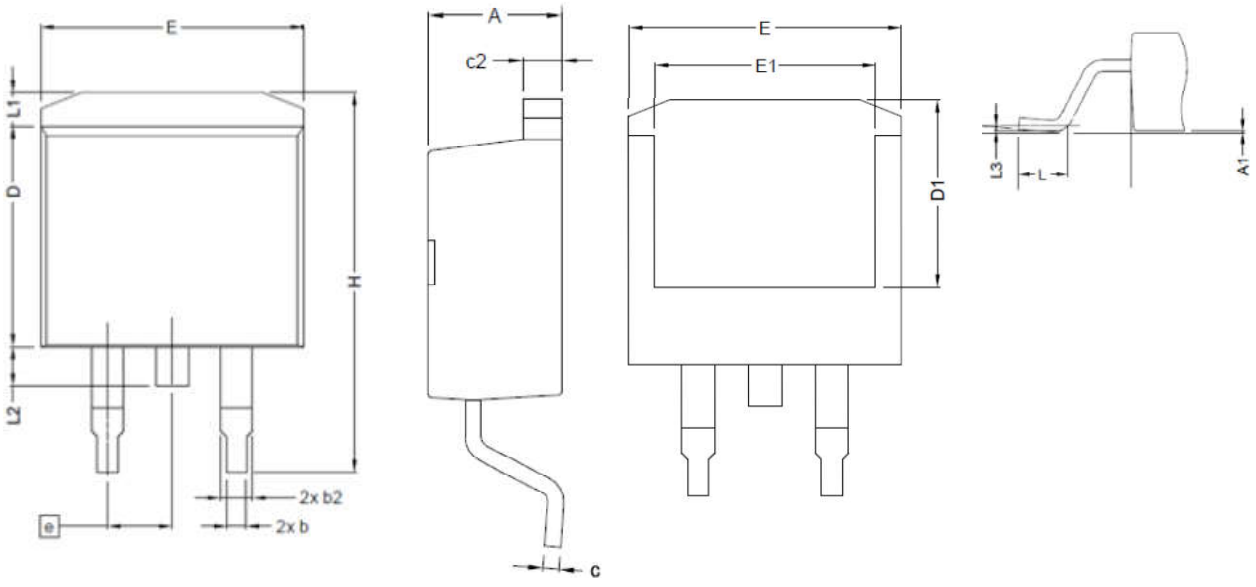
Dimensions are in millimeters, unless otherwise specified



Symbol	Millimeters(mm)	
	Min	Max
A	4.064	4.675
A1	-	0.254
b	0.508	0.99
b2	1.140	1.778
c	0.310	0.736
c2	1.140	1.650
D	8.382	9.652
D1	6.6	-
E	9.652	10.668
E1	6.223	-
e	BSC 2.54	
H	14.605	15.875
L	1.778	2.794
L1	-	1.676
L2	-	1.778
L3	BSC 0.254	

DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.